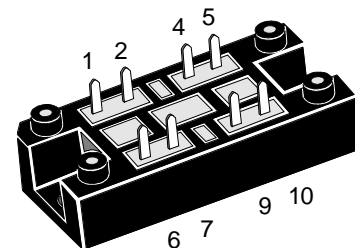
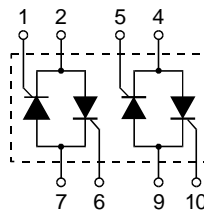


AC Controller Modules

$I_{RMS} = 2x\ 60\ A$
 $V_{RRM} = 800-1600\ V$

V_{RSM} V_{DSM} V V	V_{RRM} V_{DRM} V V	Type
800	800	VW2x60-08io1
1200	1200	VW2x60-12io1
1400	1400	VW2x60-14io1
1600	1600	VW2x60-16io1



Symbol	Test Conditions	Maximum Ratings	Features
I_{RMS}	$T_C = 85^\circ C$, 50 - 400 Hz (per phase)	60 A	<ul style="list-style-type: none"> • Thyristor controller for AC (circuit W2C acc. to IEC) for mains frequency • Soldering connections for PCB mounting • Isolation voltage 3600 V~ • Planar passivated chips • UL applied
I_{TRMS}	$T_{VJ} = T_{VJM}$	43 A	
I_{TAVM}	$T_C = 85^\circ C$; (180° sine)	27 A	
I_{TSM}	$T_{VJ} = 45^\circ C$; $V_R = 0$	t = 10 ms (50 Hz), sine 520 A t = 8.3 ms (60 Hz), sine 560 A	
I^2t	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine 470 A t = 8.3 ms (60 Hz), sine 510 A	Applications <ul style="list-style-type: none"> • Switching and control of three phase AC circuits • Softstart AC motor controller • Solid state switches • Light and temperature control
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine 1350 A ² s t = 8.3 ms (60 Hz), sine 1320 A ² s	
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50 Hz, $t_p = 200\ \mu s$ $V_D = 2/3 V_{DRM}$ $I_G = 0.45\ A$ $di_G/dt = 0.45\ A/\mu s$	repetitive, $I_T = 45\ A$ 100 A/ μs	
	$T_{VJ} = T_{VJM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	non repetitive, $I_T = I_{TAVM}$ 500 A/ μs	
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$ 1000 V/ μs	
P_{GM}	$T_{VJ} = T_{VJM}$	$t_p = 30\ \mu s$ 10 W	
	$I_T = I_{TAVM}$	$t_p = 300\ \mu s$ 5 W	
P_{GAVM}		0.5 W	
V_{RGM}		10 V	
T_{VJ}		-40...+125 °C	
T_{VJM}		125 °C	
T_{stg}		-40...+125 °C	
V_{ISOL}	50/60 Hz, RMS	t = 1 min 3000 V~	
	$I_{ISOL} \leq 1\ mA$	t = 1 s 3600 V~	
M_d	Mounting torque (M5)	2-2.5/18-22 Nm/lb.in.	
Weight	typ.	35 g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤ 5 mA
V_T	$I_T = 80$ A; $T_{VJ} = 25^\circ\text{C}$	≤ 1.65 V
V_{T0}	For power-loss calculations only	0.85 V
r_T		11 m Ω
V_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$	≤ 1.5 V
	$T_{VJ} = -40^\circ\text{C}$	≤ 1.6 V
I_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$	≤ 100 mA
	$T_{VJ} = -40^\circ\text{C}$	≤ 200 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}		≤ 5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10$ μs $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μs	≤ 450 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	≤ 200 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μs	≤ 2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20$ A, $t_p = 200$ μs ; $di/dt = -10$ A/ μs $V_R = 100$ V; $dv/dt = 15$ V/ μs ; $V_D = 2/3 V_{DRM}$	typ. 150 μs
R_{thJC}	per thyristor; DC	0.92 K/W
	per module	0.23 K/W
R_{thJK}	per thyristor; DC	1.22 K/W
	per module	0.31 K/W
d_s	Creeping distance on surface	12.7 mm
d_A	Creepage distance in air	9.4 mm
a	Max. allowable acceleration	50 m/s ²

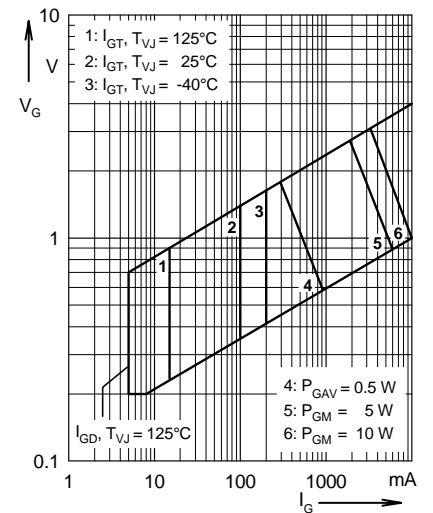


Fig. 1 Gate trigger characteristics

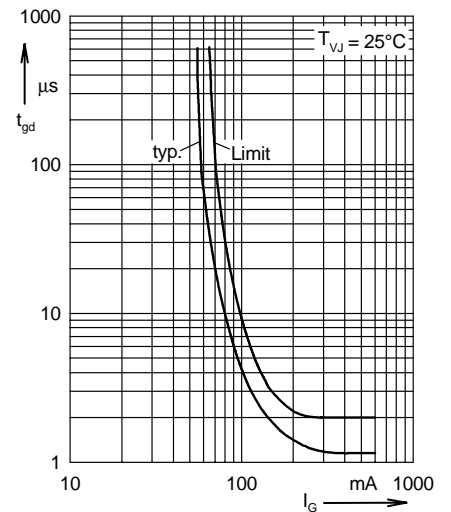


Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

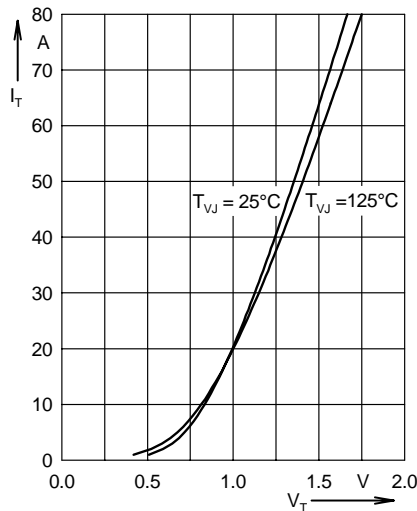
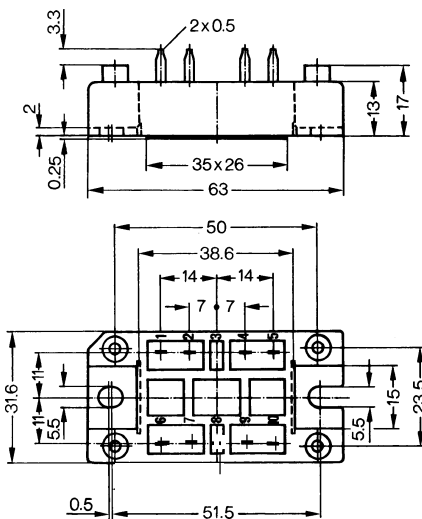


Fig. 3 Forward current versus voltage drop per leg

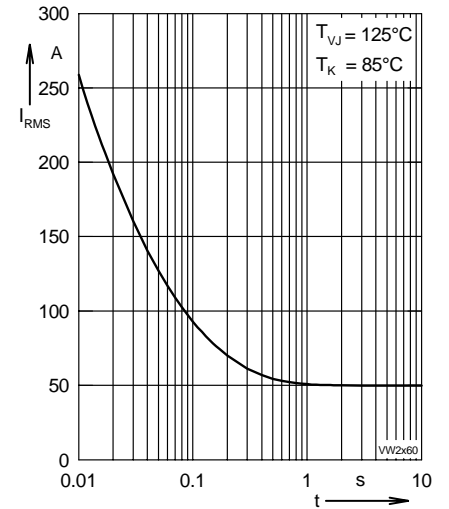


Fig. 4 Rated RMS current versus time (360° conduction)

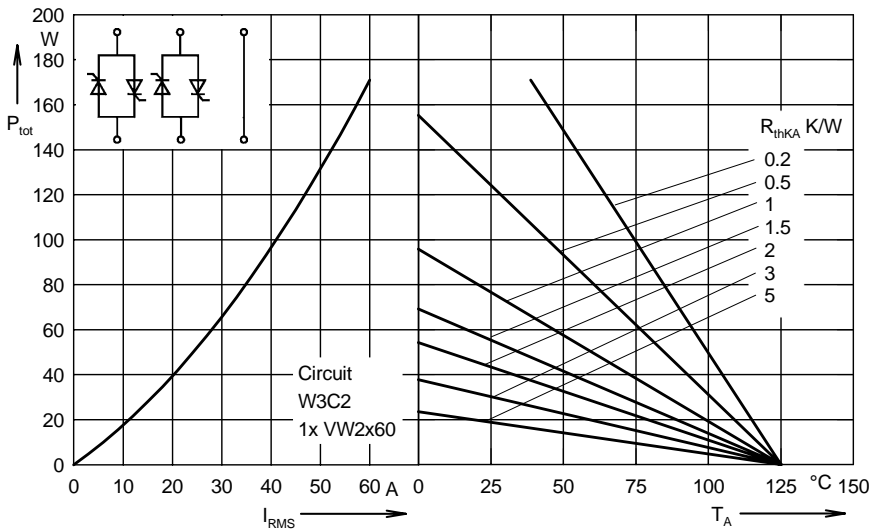


Fig. 5 Load current capability for two phase AC controller

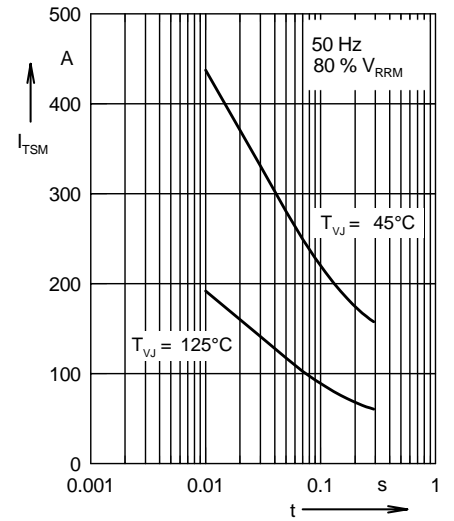


Fig. 6 Surge overload current

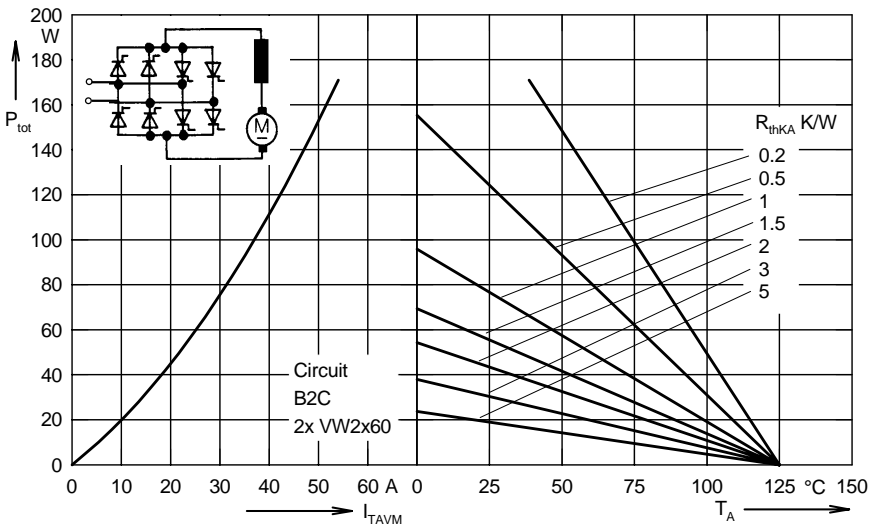


Fig. 7 Power dissipation versus direct output current and ambient temperature cyclo converter, four quadrant operation

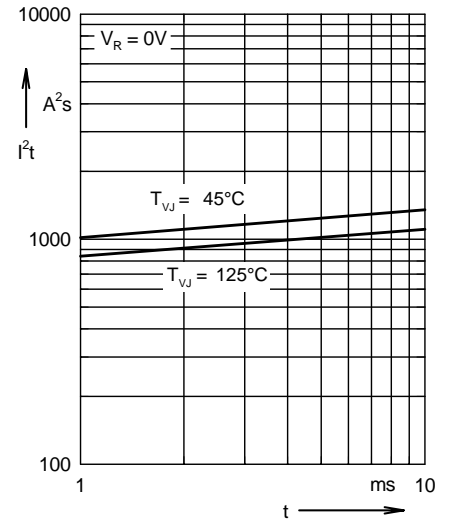


Fig. 8 I²t versus time (per thyristor)

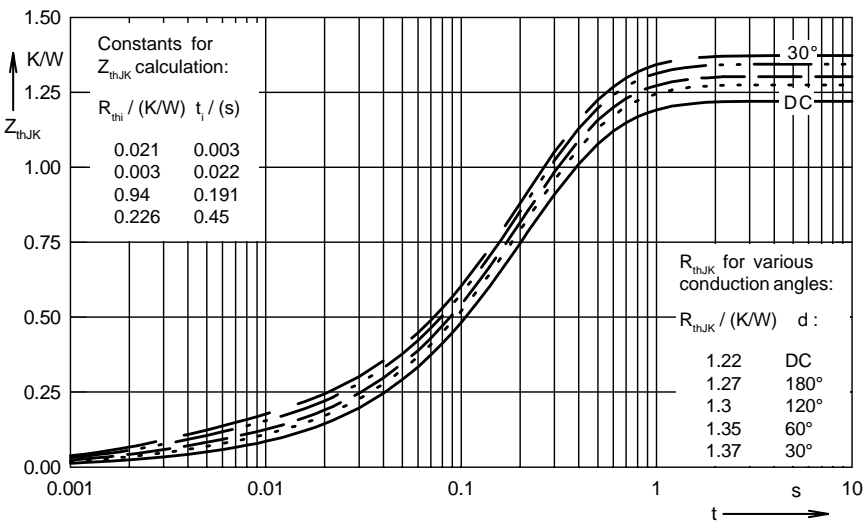


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

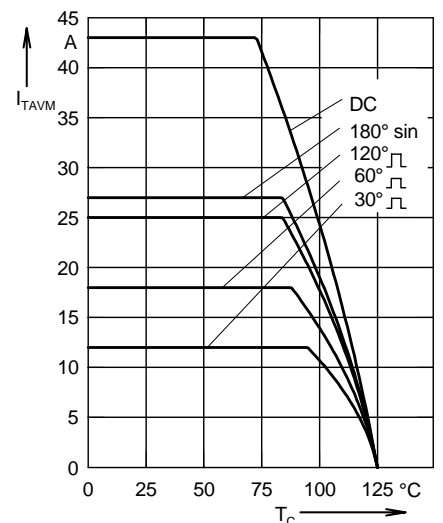


Fig. 10 Maximum forward current at case temperature